

PHASE CONTROL THYRISTORS

■ Junction Size	: Square 250 mils - IR255SG12H/ S1232
■ Wafer Size	: 4"
■ V_{RRM} Class	: 1200 V
■ Passivation Process	: Glassivated MESA
■ Reference IR Packaged Part	: n. a.

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{TM} Typical On-state Voltage	1.25V	$T_J = 25^\circ\text{C}$, $I_T = 25\text{ A}$
V_{DRM}/V_{RRM} Direct and Reverse Breakdown Voltage	1200V	$T_J = 25^\circ\text{C}$, $I_{DRM}/I_{RRM} = 100\mu\text{A}$ (1)
I_{GT} Required DC Gate Current to Trigger	5 to 80 mA	$T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load
V_{GT} Max. Required DC Gate Voltage to Trigger	2 V	$T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load
I_H Holding Current Range	5 to 100 mA	Anode supply = 6V, resistive load
I_L Maximum Latching Current	300mA	Anode supply = 6V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

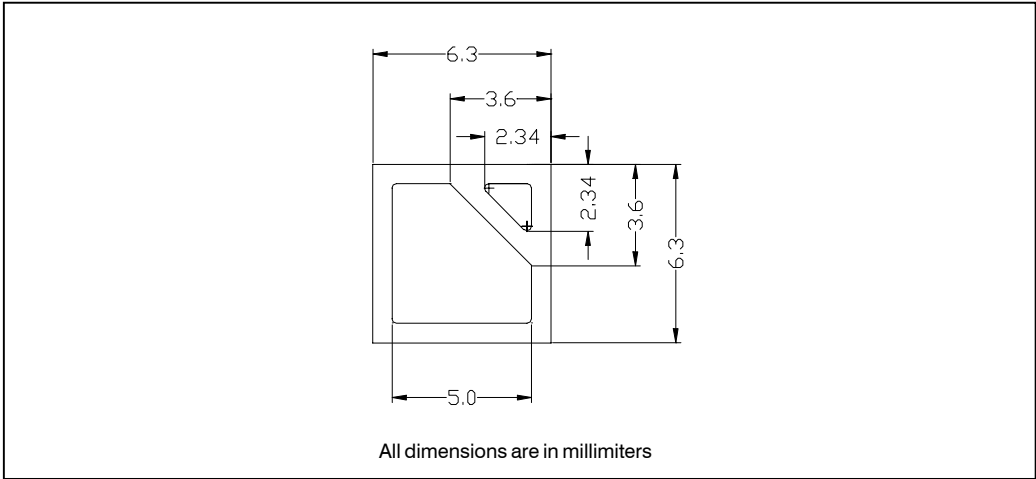
Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 15 KA)
Nominal Front Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 15 KA)
Chip Dimensions	250x250mils (see drawing)
Wafer Diameter	100mm, with std. <110> flat
Wafer Thickness	$330\mu\text{m} \pm 10\mu\text{m}$
Maximum Width of Sawing Line	$130\mu\text{m}$
Reject Ink Dot Size	0.25mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

S1232

Bulletin I0141J 01/01

International
IR Rectifier

Outline Table



Wafer Layout

